

Wafer Spec Sheet

Sheet No. :GPP-0062

Rev. :1.0

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Wafer Type : Planar 600V

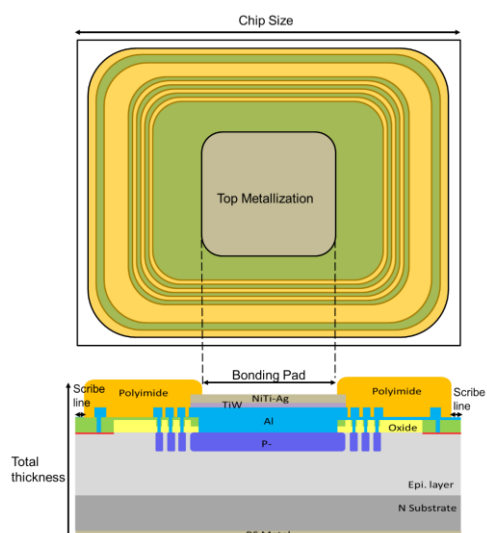
P / N : 6PG1100600SSK-NP

☐ Advance

☐ Preliminary

☒ Production

Chip Drawing



Mechanical Parameters

Chip Size	mil	110 x 110mil (2794 x 2794um)
Wafer Size	inch	6
Bonding Pad	um	2220um
Top Metallization	um	Al/TiW/TiNi/Ag (3.0-0.15-0.2-2.0um)
Back Metallization	um	TiNi/Ag (0.2-0.8um)
Total thickness	um	250 ± 20um
Gross Dies	pcs/wafer	2020
Termination area	☐ Field Plate ☒ Floating Ring	
SCRIBE LINE WIDTH	um	60um

ELECTRICAL CHARACTERISTICS @ TA = 25°C

Parameter	Min.	Typical	Max.	Unit	Test Condition
Forward Voltage (VF)	---	0.750	0.790	V	IF = 1.5A
Forward Voltage (VF)	---	0.790	0.830	V	IF = 3.0A
Forward Voltage (VF)	---	0.845	0.890	V	IF = 6.0A
Forward Voltage (VF)	---	0.720	0.770	V	IF = 6.0A @ TA = 125°C
Forward Voltage (VF)	---	0.87	0.900	V	IF = 7.5A
Reverse Breakdown Voltage	660	780	---	V	IR1 = 0.10 mA
Reverse Breakdown Voltage	660	780	---	V	IR2 = 0.50 mA
Reverse Current	---	0.005	0.05	uA	VR1 = 600 V
Reverse Current	---	0.005	0.05	uA	VR2 = 630 V
Reverse recovery time	---	310	370	uA	RG1

Note :

(1) DVB<10V at VB1-VB2

(2) TJ(max.)=175C